## 100 學年第1 學期 電子薄膜科技

## Electronic thin film Technology 課程綱要

課程名稱:(中文)電子薄膜科技			開課單位		工科系	
(英文)Electronic thin film Technology			科號 Course Number			
任課教師: 歐陽汎怡						
學分	3	必/選修	選修	開課年級	研究所課程	
先修科目或先備能力:						
建議先修習薄膜工程導論 (Introduction to Thin Film Engineering)						
課程說明(Course Description): It is well known that thin films are widely used in the electronic industry. Due to the trend on miniaturization of electronic devices, nanosclae electronic devices are needed and the technology and reliability of thin films have recently attracted increasing attentions. This course will focuses on the science and process of thin films, and reliability science for thin film application in the electronic industry. The topics will cover: 1. Fundamental topic in thin-film process: deposition, surface energy and atomic diffusion 2. Application of diffusion equations (Fick's first law and Fick's second law) 3. Theoretical and practical understanding of electronic thin-film reliability: electromigration,						
thermomigration and	stress-mig	ration				
指定用書(Text Books)	"Electronic ISBN 978-0	c Thin-Film Reliability", )-521-51613-6.	King-Nin	g Iu, Cambridge University	Press, 2010,	
參考書籍(References)	1. "Thin fil 2. "Electro King-Ning 3. "Microe Nostrand F 4. "微電子	m deposition" Donald nic thin film Science fo Tu, James W. Mayer, a lectronics packaging h Reinhold, 1989 材料與製程,陳力俊	L. Smith, rr electric nd Leona andbook 主編中国	MC Graw Hill, 1999. al engineers and materials : ird C. Feldman, MACMILLAN "R.R. Tummala and E.J. Ryn 国材料科學學會 2000	scientists" I, 1992. naszewski, Van	
教學要點概述:						
<ol> <li>教學方式(Teaching M</li> </ol>	ethod): 投景	影片(上網)教學及隨堂	筆記			
<ol> <li>成績考核(Evaluation)</li> <li>(1) 學期作業 Homework</li> </ol>	: ork :15%					
(2) Midterm 30%						
(3) Final exam:30%						
(4) Presentation :25%						
3.教學進度表						
週內容						

週次	內容				
1	Introduction : Thin Film Applications to Microelectronic Technology				
2	Thin Film Deposition				
	✓ Flux equation of thin film deposition/ thin film deposition rate				
	✓ Kinetic energy of gas molecules/ frequency of collision of gas molecules				
	✓ Bolzmann's velocity distribution function and ideal gas law				

	✓ Maxwell's velocity distribution function and kinetic energy of gas molecules					
	Surface Energy in Thin Films					
3	✓ Surface energy and surface tension					
	<ul> <li>Liquid surface energy measured by capillary effect</li> </ul>					
	Solid surface energy measured by zero creep					
	<ul> <li>✓ Magnitude of surface energies</li> </ul>					
4	Surface Kinetic Processes on Thin Films					
	✓ Surface diffusion					
	<ul> <li>Step mediated growth in homoepitaxy</li> <li>Unsequences and participation of a surface disc.</li> </ul>					
	Monogeneous nucleation of a surface usc     Mass transport on patterned surfaces					
	<ul> <li>Ripening of a hemispherical particle on a surface</li> </ul>					
	Atomic Diffusion in Crystalline Solids /Application of diffusion equation					
5	$\checkmark$ Fick's first law and applications of Fick's first law (Zener's and Kidson's analysis)					
	Fick's second law applications of Fick's secondt law (Darken's analysis/ Boltzmann and Matano's					
	analysis/ Kirkendall void formation)					
	✓ Diffusion coefficient (parameters in diffusion coefficient/ calculation of diffusion coefficient)					
	Applications of Diffusion Equation/ Grain Boundary Diffusion					
6	<ul> <li>Analysis of growth of a solid precipitate (Ham's model)</li> </ul>					
	✓ Fisher ★ s analysis of grain boundary diffusion					
	✓ Whipple ★ s analysis of grain boundary diffusion					
	Elastic Stress and Strain in Thin Films					
	✓ Biaxial stress in thin films					
7	✓ The origin of intrinsic stress in thin films					
	Stoney * s equation of biaxial stress in thin films					
	Measurement of thermal stress in Al thin films					
	Application of stoney * s equation to thermal expansion measurement					
	Interdiffusion and Reaction in Thin Films					
8	<ul> <li>Sincide formation</li> <li>Kinetics of interfacial-reaction-controlled growth in thin film reactions</li> </ul>					
	✓ Marker analysis in intermetallic compound formation					
Q	Midterm					
	Reliability. Electroningration in Metals					
10	Concent and physical mechanism for electromigration					
	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> </ul>					
	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> </ul>					
	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> </ul>					
	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> </ul>					
11	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> </ul> Reliability: Electromigration induced failure in Al and Cu Interconnects <ul> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> </ul>					
11	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> <li>Void formation in the low current density region</li> </ul>					
11	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> <li>Void formation in the low current density region</li> <li>Electromigration induced failure in Al interconnects and Cu interconnects (microstructure, Mean time to follow otc)</li> </ul>					
11	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> <li>Void formation in the low current density region</li> <li>Electromigration induced failure in Al interconnects and Cu interconnects (microstructure, Mean time to failure etc)</li> </ul>					
11	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> <li>Void formation in the low current density region</li> <li>Electromigration induced failure in Al interconnects and Cu interconnects (microstructure, Mean time to failure etc)</li> <li>Reliability: Thermomigration:</li> </ul>					
11	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> <li>Void formation in the low current density region</li> <li>Electromigration induced failure in Al interconnects and Cu interconnects (microstructure, Mean time to failure etc)</li> <li>Reliability: Thermomigration:</li> <li>Concept and physical mechanism for thermomigration</li> </ul>					
11	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> <li>Void formation in the low current density region</li> <li>Electromigration induced failure in Al interconnects and Cu interconnects (microstructure, Mean time to failure etc)</li> <li>Reliability: Thermomigration:</li> <li>Concept and physical mechanism for thermomigration</li> <li>Thermomigration in flip chip solder joints of SnPb</li> <li>Thermomigration in flip chip solder ioints of Ph-fee</li> </ul>					
11 12	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> <li>Void formation in the low current density region</li> <li>Electromigration induced failure in Al interconnects and Cu interconnects (microstructure, Mean time to failure etc)</li> <li>Reliability: Thermomigration:</li> <li>Concept and physical mechanism for thermomigration</li> <li>Thermomigration in flip chip solder joints of SnPb</li> <li>Thermomigration in flip chip solder joints of Pb-fee</li> </ul>					
11 12 13	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> <li>Void formation in the low current density region</li> <li>Electromigration induced failure in Al interconnects and Cu interconnects (microstructure, Mean time to failure etc)</li> <li>Reliability: Thermomigration:</li> <li>Concept and physical mechanism for thermomigration</li> <li>Thermomigration in flip chip solder joints of SnPb</li> <li>Thermomigration in flip chip solder joints of Pb-fee</li> <li>Company Visiting- TSMC-tentative</li> </ul>					
11 12 13	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> <li>Void formation in the low current density region</li> <li>Electromigration induced failure in Al interconnects and Cu interconnects (microstructure, Mean time to failure etc)</li> <li>Reliability: Thermomigration:</li> <li>Concept and physical mechanism for thermomigration</li> <li>Thermomigration in flip chip solder joints of SnPb</li> <li>Thermomigration in flip chip solder joints of Pb-fee</li> <li>Company Visiting- TSMC-tentative</li> <li>Reliability: Stress Migration in Thin Films</li> </ul>					
11 12 13 14	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> <li>Void formation in the low current density region</li> <li>Electromigration induced failure in Al interconnects and Cu interconnects (microstructure, Mean time to failure etc)</li> <li>Reliability: Thermomigration:</li> <li>Concept and physical mechanism for thermomigration</li> <li>Thermomigration in flip chip solder joints of SnPb</li> <li>Thermomigration in flip chip solder joints of Pb-fee</li> <li>Company Visiting- TSMC-tentative</li> <li>Reliability: Stress Migration in Thin Films</li> <li>Concept of chemical potential in a stress solid and diffusion creep</li> <li>Void growth in Al interconnect driven by tencile stress</li> </ul>					
11 12 13 14	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> <li>Void formation in the low current density region</li> <li>Electromigration induced failure in Al interconnects and Cu interconnects (microstructure, Mean time to failure etc)</li> <li>Reliability: Thermomigration:</li> <li>Concept and physical mechanism for thermomigration</li> <li>Thermomigration in flip chip solder joints of SnPb</li> <li>Thermomigration in flip chip solder joints of Pb-fee</li> <li>Company Visiting- TSMC-tentative</li> <li>Reliability: Stress Migration in Thin Films</li> <li>Concept of chemical potential in a stress solid and diffusion creep</li> <li>Void growth in Al interconnect driven by tensile stress</li> <li>Whisker growth in Sn/Cu thin films driven by compressive stress</li> </ul>					
11 12 13 14	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> <li>Void formation in the low current density region</li> <li>Electromigration induced failure in Al interconnects and Cu interconnects (microstructure, Mean time to failure etc)</li> <li>Reliability: Thermomigration:</li> <li>Concept and physical mechanism for thermomigration</li> <li>Thermomigration in flip chip solder joints of SnPb</li> <li>Thermomigration in flip chip solder joints of Pb-fee</li> <li>Company Visiting- TSMC-tentative</li> <li>Reliability: Stress Migration in Thin Films</li> <li>Concept of chemical potential in a stress solid and diffusion creep</li> <li>Void growth in Al interconnect driven by tensile stress</li> <li>Whisker growth in Sn/Cu thin films driven by compressive stress</li> </ul>					
11 12 13 14	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> <li>Void formation in the low current density region</li> <li>Electromigration induced failure in Al interconnects and Cu interconnects (microstructure, Mean time to failure etc)</li> <li>Reliability: Thermomigration:</li> <li>Concept and physical mechanism for thermomigration</li> <li>Thermomigration in flip chip solder joints of SnPb</li> <li>Thermomigration in flip chip solder joints of Pb-fee</li> <li>Company Visiting- TSMC-tentative</li> <li>Reliability: Stress Migration in Thin Films</li> <li>Concept of chemical potential in a stress solid and diffusion creep</li> <li>Void growth in Al interconnect driven by tensile stress</li> <li>Whisker growth in Sn/Cu thin films driven by compressive stress</li> <li>Reliability: Irreversible Processes in Interconnect and Packaging Technology</li> </ul>					
11 12 13 14	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> <li>Void formation in the low current density region</li> <li>Electromigration induced failure in Al interconnects and Cu interconnects (microstructure, Mean time to failure etc)</li> <li>Reliability: Thermomigration:</li> <li>Concept and physical mechanism for thermomigration</li> <li>Thermomigration in flip chip solder joints of SnPb</li> <li>Thermomigration in flip chip solder joints of Pb-fee</li> <li>Company Visiting- TSMC-tentative</li> <li>Reliability: Stress Migration in Thin Films</li> <li>Concept of chemical potential in a stress solid and diffusion creep</li> <li>Void growth in Al interconnect driven by tensile stress</li> <li>Whisker growth in Sn/Cu thin films driven by compressive stress</li> <li>Reliability: Irreversible Processes in Interconnect and Packaging Technology</li> <li>Entropy production due to heat conduction/ atomic diffusion/ electrical condition</li> </ul>					
11 12 13 14 15	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure in Al and Cu Interconnects</li> <li>Void formation in the low current density region</li> <li>Electromigration induced failure in Al interconnects and Cu interconnects (microstructure, Mean time to failure etc)</li> <li>Reliability: Thermomigration:</li> <li>Concept and physical mechanism for thermomigration</li> <li>Thermomigration in flip chip solder joints of SnPb</li> <li>Thermomigration in flip chip solder joints of Pb-fee</li> <li>Company Visiting- TSMC-tentative</li> <li>Reliability: Stress Migration in Thin Films</li> <li>Concept of chemical potential in a stress solid and diffusion creep</li> <li>Void growth in Al interconnect driven by tensile stress</li> <li>Whisker growth in Sn/Cu thin films driven by compressive stress</li> <li>Reliability: Irreversible Processes in Interconnect and Packaging Technology</li> <li>Entropy production due to heat conduction/ atomic diffusion/ electrical condition</li> <li>Irreversible process in electromigration/ thermomigration</li> </ul>					
11 12 13 14 15 16	<ul> <li>Concept and physical mechanism for electromigration</li> <li>The effect of back stress in electromigration and how to measurement it</li> <li>Current crowding effect and current density gradient force of electromigration</li> <li>Reliability: Electromigration induced failure in Al and Cu Interconnects</li> <li>Electromigration induced failure due to atomic flux divergence</li> <li>Electromigration induced failure due to electric current crowding</li> <li>Void formation in the low current density region</li> <li>Electromigration induced failure in Al interconnects and Cu interconnects (microstructure, Mean time to failure etc)</li> <li>Reliability: Thermomigration:</li> <li>Concept and physical mechanism for thermomigration</li> <li>Thermomigration in flip chip solder joints of SnPb</li> <li>Thermomigration in flip chip solder joints of Pb-fee</li> <li>Company Visiting- TSMC-tentative</li> <li>Reliability: Stress Migration in Thin Films</li> <li>Concept of chemical potential in a stress solid and diffusion creep</li> <li>Void growth in Al interconnect and Packaging Technology</li> <li>Entropy production due to heat conduction/ atomic diffusion/ electrical condition</li> <li>Irreversible processe in electronicy atomic diffusion/ electrical condition</li> <li>Irreversible process in electromigration/ thermomigration</li> </ul>					

	<ul> <li>✓ Physical analysis of electromigration failure in flip chip solder joints</li> <li>✓ Statistical analysis of electromigration in flip chip solder joints</li> </ul>
17	<ul> <li>Group presentation</li> <li>✓ Students will need to give a presentation related to thin film application in the industry.</li> </ul>
18	Final Exam

